

**IN THE SPECIFICATION:**

Please amend paragraph [0001] as follows:

[0001] This application is a divisional of application Serial No. 09/559,153, filed April 26, 2000, ~~pending~~, now U.S. Patent 6,387,717, issued May 14, 2002.

Please amend paragraph [0014] as follows:

[0014] A variety of low work function materials can be incorporated into the field emission tips of the present invention. Such low work function materials include, but are not limited to,  $\text{AlTiSi}_x$  (aluminum titanium silicide [wherein  $x$  is generally between 1 and 4]),  $\text{TiSi}_x\text{N}$  (titanium silicide nitride),  $\text{TiN}$  (titanium nitride),  $\text{Cr}_3\text{Si}$  (tri-chromium mono-silicon),  $\text{TaN}$  (tantalum-nitride), or the like. Moreover, other low work function materials, such as metals including cesium (Ce), and cermets including  $\text{Cr}_3\text{Si-SiO}_2$  (tri-chromium mono-silicon-silicon-dioxide), silicon-dioxide,  $\text{Cr}_3\text{Si-MgO}$  (tri-chromium mono-silicon magnesium-oxide),  $\text{Au-SiO}_2$  (gold-silicon-dioxide), silicon-dioxide, and  $\text{Au-MgO}$  (gold magnesium oxide), may also be used.

Please amend paragraph [0034] as follows:

[0034] FIGs. 10-16 illustrate still another embodiment for forming field emission tips according to the present invention. As shown in FIG. 10, a low work function material 112 is deposited on a substrate 102. An etch mask material is patterned to form etch mask element 104 on the low work function material 112, as shown in FIG. 11. The low work function material 112 and substrate 102 are then anisotropically etched by known techniques (e.g., high density plasma etching, RIE, MIE, MERIE, PE, point plasma etching, PERIE, or ECR) to form a vertical column 106 of substantially constant cross-section from the portion of the substrate 102 and the low work function material 112 protected by etch mask element 104, as shown in FIG. 12. Etch mask element 104 is then removed, as shown in FIG. 13. A sacrificial material 122, such as silicon dioxide or tetraethyl orthosilicate (TEOS), is then conformally deposited over the vertical column 106 capped with the low work function material 112 to form a

covered structure 124, as shown in FIG. 14. The covered structure 124 is then facet etched, such as by the same techniques as those described previously herein with respect to FIGs. 1-4, to form a low work function material-tipped field emission tip 130, as shown in FIG. 15. As also shown in FIG. 15, a redeposition material 126 produced during the facet etch, comprising a mixture of material from the vertical column 106, the low work function material 112, and the sacrificial material 122, collects in exposed corners 128 of the sacrificial material 122 at a junction of the vertical column 106 and the base substrate 102 during the facet etch. Although such redeposition material 126 would be difficult to remove if deposited directly on the vertical column 106 and the base substrate 102 surfaces, the presence of the sacrificial material 122 under the ~~redeposited~~ redeposition material 126 allows the redeposition material 126 to be removed with a clean-up technique, as illustrated in FIG. 16, such as by a hydrofluoric acid (HF) dip or diluted HF dip, as known in the art. The mask element is then removed, as known in the art, to expose a cleaned, low work function material-tipped field emission tip 132.